

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A method of polishing and then cleaning substrates, comprising:
 polishing a first substrate by pressing said first substrate against a first polishing surface;
then
 primarily cleaning said first substrate in a first of two first cleaning units; then
 secondarily cleaning said first substrate in a common second cleaning unit while
supporting said first substrate on a table;
 polishing a second substrate by pressing said second substrate against a second polishing surface; then
 primarily cleaning said second substrate in a second of said two first cleaning units; and
then
 secondarily cleaning said second substrate in said common second cleaning unit while
supporting said second substrate on said table.

Claims 2-9 (Cancelled)

10. (Previously presented) The method according to claim1, wherein
 primarily cleaning said first substrate in said first of said two first cleaning units
comprises cleaning said first substrate in said first of said two first cleaning units by subjecting
said first substrate to a first cleaning function, and
 primarily cleaning said second substrate in said second of said two first cleaning units
comprises cleaning said second substrate in said second of said two first cleaning units by
subjecting said second substrate to a second cleaning function that is the same as said first
cleaning function.

11. (Previously presented) The method according to claim 1, further comprising:
drying said first substrate and said second substrate after secondarily cleaning said first substrate and said second substrate.

12. (Previously presented) The method according to claim 1, wherein
primarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate, or
secondarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate.

13. (Previously presented) The method according to claim 1, wherein
primarily cleaning said first substrate in said first of said two first cleaning units
comprises primarily cleaning said first substrate in said first of said two first cleaning units for a time period that is greater than a time period for which said first substrate is secondarily cleaned in said common second cleaning unit, and
primarily cleaning said second substrate in said second of said two first cleaning units
comprises primarily cleaning said second substrate in said second of said two first cleaning units for a time period that is greater than a time period for which said second substrate is secondarily cleaned in said common second cleaning unit.

14. (Previously presented) The method according to claim 1, wherein
primarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid, or
secondarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid.

15. (Previously presented) The method according to claim 1, wherein primarily cleaning said first substrate and primarily cleaning said second substrate comprises primarily cleaning said first substrate in parallel with primarily cleaning said second substrate.

Claims 16-21 (Cancelled)

22. (Previously presented) The method according to claim 1, wherein polishing said first substrate and polishing said second substrate comprises polishing said first substrate in parallel with polishing said second substrate.

23. (Previously presented) The method according to claim 1, further comprising: not pressing said first substrate against said second polishing surface.

24. (Previously presented) The method according to claim 23, further comprising: not cleaning said first substrate in said second of said two first cleaning units.

25. (Previously presented) The method according to claim 24, further comprising: not pressing said second substrate against said first polishing surface.

26. (Previously presented) The method according to claim 25, further comprising: not cleaning said second substrate in said first of said two first cleaning units.

27. (Previously presented) The method according to claim 23, wherein primarily cleaning said first substrate in said first of said two first cleaning units comprises cleaning said first substrate in said first of said two first cleaning units by subjecting said first substrate to a first cleaning function, and

primarily cleaning said second substrate in said second of said two first cleaning units comprises cleaning said second substrate in said second of said two first cleaning units by subjecting said second substrate to a second cleaning function that is the same as said first cleaning function.

28. (Previously presented) The method according to claim 23, further comprising:
drying said first substrate and said second substrate after secondarily cleaning said first substrate and said second substrate.

29. (Previously presented) The method according to claim 23, wherein
primarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate, or
secondarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate.

30. (Previously presented) The method according to claim 23, wherein
primarily cleaning said first substrate in said first of said two first cleaning units comprises primarily cleaning said first substrate in said first of said two first cleaning units for a time period that is greater than a time period for which said first substrate is secondarily cleaned in said common second cleaning unit, and
primarily cleaning said second substrate in said second of said two first cleaning units comprises primarily cleaning said second substrate in said second of said two first cleaning units for a time period that is greater than a time period for which said second substrate is secondarily cleaned in said common second cleaning unit.

31. (Previously presented) The method according to claim 23, wherein
primarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid, or

secondarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid.

32. (Previously presented) The method according to claim 23, wherein primarily cleaning said first substrate and primarily cleaning said second substrate comprises primarily cleaning said first substrate in parallel with primarily cleaning said second substrate.

33. (Previously presented) The method according to claim 1, further comprising: not cleaning said first substrate in said second of said two first cleaning units.

34. (New) The method according to claim 1, wherein secondarily cleaning said first substrate comprises supplying water to said first substrate while said first substrate is rotated via rotation of said table, and secondarily cleaning said second substrate comprises supplying water to said second substrate while said second substrate is rotated via rotation of said table.